

IEEE

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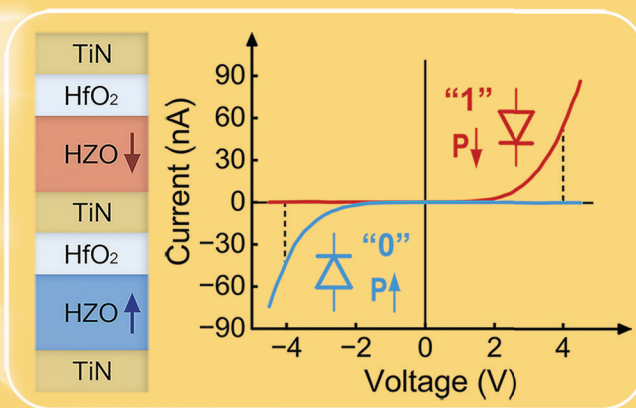
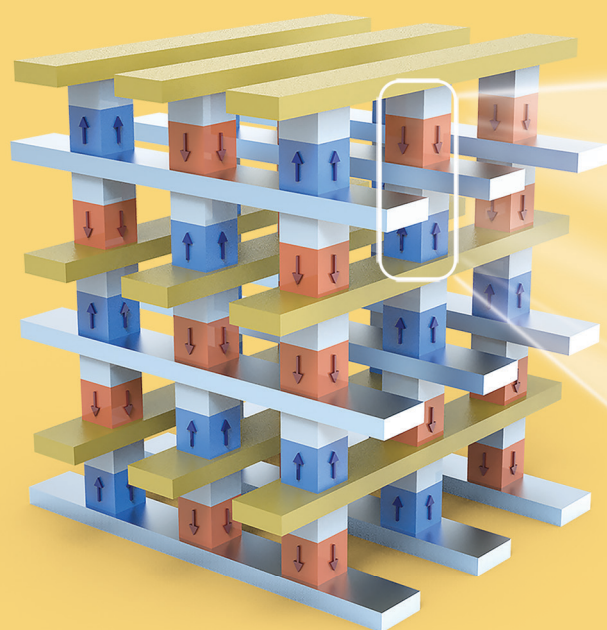
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Featured Article: All-ALD Sequential Monolithic Integration of Selector-Free Five-Layer Ferroelectric Diodes for 3-D Cross-Point Memory



Editor's Highlights:

- Role of Interlayer and Interfacial Traps in Endurance Degradation of FeFETs (Memory Devices and Technology)
- Dielectric Deposition Enhanced Crystallization in Atomic-Layer-Deposited Indium Oxide Transistors Achieving High Gate-Hall Mobility Exceeding 100 cm²/V·s at Room Temperature (Thin-Film Transistors)
- Avalanche-Triggered Dynistor for Simplified Driving of High-Voltage and High-Current Pulsed-Power Switch Stack (Solid-State Power and High-Voltage Devices)
- High-Gain Hydrogen-Terminated Diamond Logic Circuits With Low Power-Consumption (Emerging Technologies and Devices)



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